

# PSMN7R5-60YL

N-channel 60 V, 7.5 m $\Omega$  logic level MOSFET in LFPAK56 Product data sheet

#### 1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

#### 2. **Features and benefits**

- Advanced TrenchMOS provides low R<sub>DSon</sub>and low gate charge
- Logic level gate operation
- Avalanche rated, 100% tested
- LFPAK provides maximum power density in a Power SO8 package

#### **Applications** 3.

- Synchronous rectifier in LLC topology
- Chargers & adaptors with V<sub>out</sub> < 10 V
- Fast charge & USB-PD applications
- Battery powered motor control
- LED lighting & TV backlight

#### Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	60	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	-	86	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	147	W
Tj	junction temperature		-55	-	175	°C
Static char	acteristics		'			
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 20 A; $T_j$ = 25 °C; Fig. 11	-	6	7.5	mΩ
Dynamic cl	haracteristics		'			
Q <sub>G(tot)</sub>	total gate charge	$V_{GS}$ = 10 V; $I_D$ = 20 A; $V_{DS}$ = 48 V; $T_j$ = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	60.6	-	nC
$Q_{GD}$	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 20 \text{ A}; V_{DS} = 48 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 13; Fig. 14$	-	9.7	-	nC



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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 86 A; $V_{sup} \le$ 60 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[1][2]	-	-	76.5	mJ

- Single-pulse avalanche rating limited by maximum junction temperature of 175  $^{\circ}\text{C}.$  Refer to application note AN10273 for further information.

## **Pinning information**

Table 2. **Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	d	G 4
4	G	gate	gggg	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

## **Ordering information**

Table 3. **Ordering information** 

Type number	Package				
	Name	Description	Version		
PSMN7R5-60YL	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

## **Limiting values**

Table 4. **Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

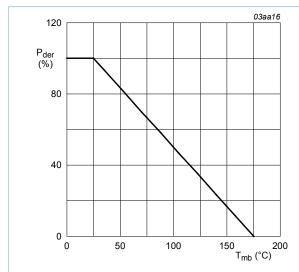
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	60	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 k $\Omega$	-	60	V
$V_{GS}$	gate-source voltage		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	147	W
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>	-	86	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>	-	61	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 3	-	346	Α

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Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	diode					,
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	86	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$		-	346	Α
Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 86 A; $V_{sup} \le$ 60 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[1][2]	-	76.5	mJ

- Single-pulse avalanche rating limited by maximum junction temperature of 175  $^{\circ}\text{C}.$  Refer to application note AN10273 for further information.



Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

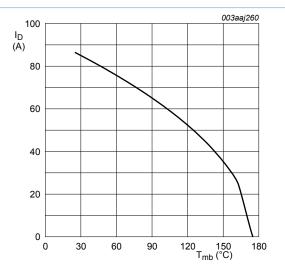


Fig. 2. Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

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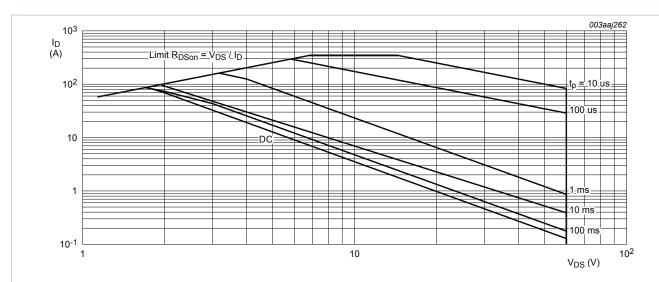
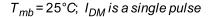


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



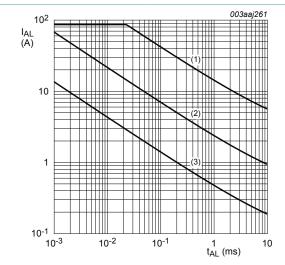


Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

(1) 
$$T_{j(init)} = 25^{\circ}C$$
; (2)  $T_{j(init)} = 150^{\circ}C$ ; (3) Repetitive Avalanche

#### 8. Thermal characteristics

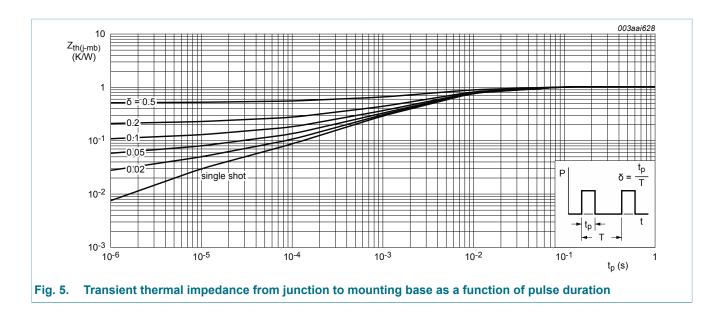
Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	1.02	K/W

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### 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Mi	n T	ур	Max	Unit
Static chara	acteristics						
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	) -		-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-		-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 9; Fig. 10	1.	4 1	.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-		2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	0.	5 -		-	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-		500	μA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	C	0.05	10	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	2	100	nA
		V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	6	8.8	8.7	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; Fig. 11	-	6	6	7.5	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	-	-		19.7	mΩ
Dynamic ch	aracteristics		1				
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 20 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 5 V; T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	3	31	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I <sub>D</sub> = 20 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	60.6	-	nC
$Q_{GS}$	gate-source charge	I <sub>D</sub> = 20 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 5 V;	-	9	-	nC
$Q_{GD}$	gate-drain charge	T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	9.7	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	3435	4570	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	295	355	pF
C <sub>rss</sub>	reverse transfer capacitance		-	150	205	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 45 \text{ V}; R_L = 2 \Omega; V_{GS} = 5 \text{ V};$	-	17	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$	-	30	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	42	-	ns
t <sub>f</sub>	fall time		-	26	-	ns
Source-dra	in diode		l	l		
$V_{SD}$	source-drain voltage	$I_S = 20 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$	-	0.82	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	24	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V; T <sub>j</sub> = 25 °C	-	22.3	-	nC

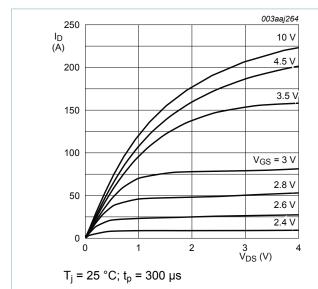


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

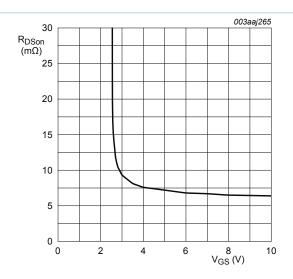


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
°C;  $I_D = 20A$ 

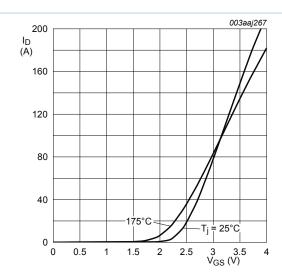


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

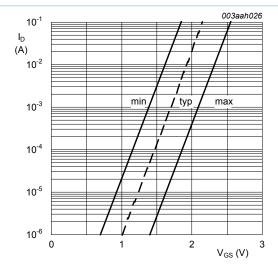


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

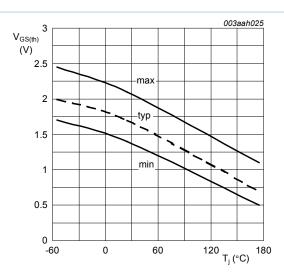
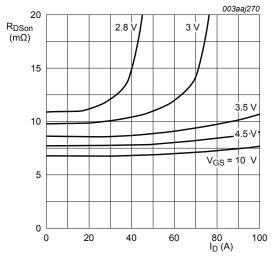


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D$$
 = 1 mA;  $V_{DS}$  =  $V_{GS}$ 



 $T_j = 25 \, ^{\circ}C; t_p = 300 \, \mu s$ 

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

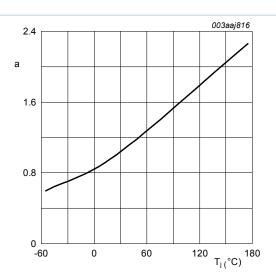


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}C)}$$

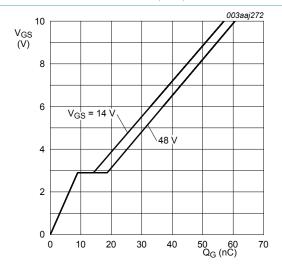


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 20A$$

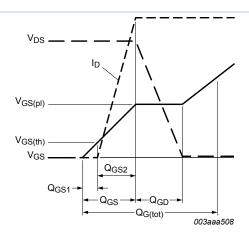


Fig. 13. Gate charge waveform definitions

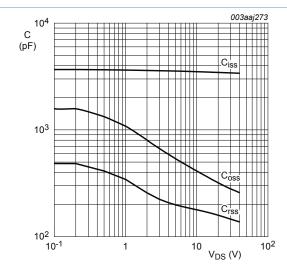


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V$$
;  $f = 1MHz$ 

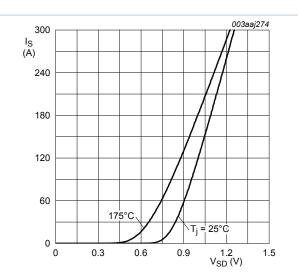
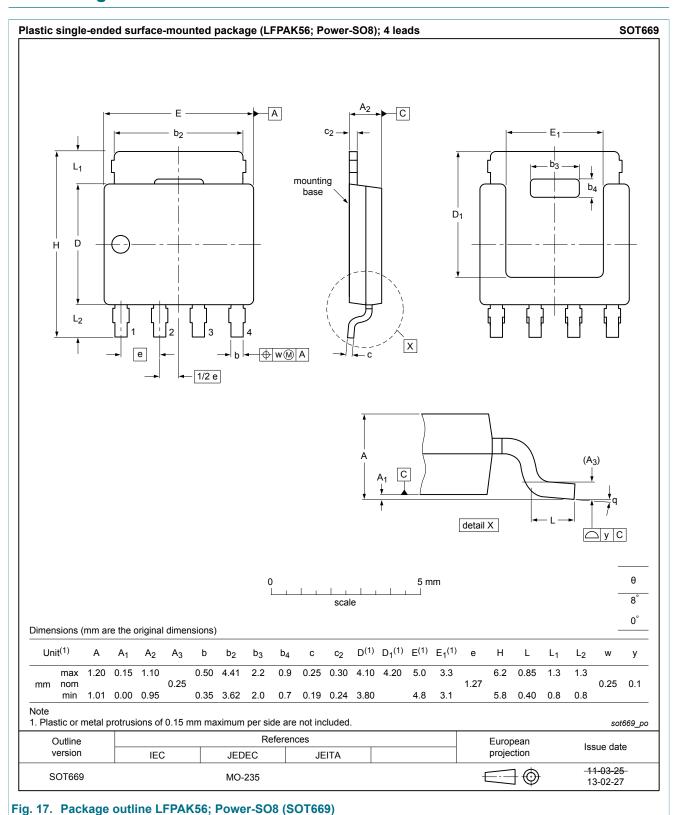


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values  $V_{\rm GS} = 0V$ 

N-channel 60 V, 7.5 mΩ logic level MOSFET in LFPAK56

### 10. Package outline



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#### N-channel 60 V, 7.5 mΩ logic level MOSFET in LFPAK56

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Product [short] data sheet	Production	This document contains the product specification.

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